| INFORI | MATION DISCLOSURE | ATTY. | DOCKET NO. | SERIAL NO. | | | |
|-------------------------|--|---|---|--|--|--|-----------------|
| IPE | CITATION | 925-2 | 287 | 10/809,681 | | | |
| 85 | | APPLIC | | · · · · · · · · · · · · · · · · · · · | | | |
| 2 2 2004 | | SHIN | NGUBARA, S. et al. | | | | |
| 87 | e several sheets if necessary) | FILING | DATE | GROUP | | | |
| ADEM ARK ON | | Marc | ch 26, 2004 | 1762 | | | |
| | | (| J.S. PATENT DOCUMENTS | | | | |
| EXAMINER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | | DATE OPRIATE |
| | | | | | | | |
| | | | | | | | |
| | + + | | | | | | ~ |
| | | | | | | | |
| | | | | | | İ | · . |
| | | | | | | | |
| | | | | | | | |
| | | | | | <u> </u> | | |
| | | | | · | | | |
| | | | | | | | |
| <u> </u> | | | | | | | |
| | | | | | | | |
| | | | | | | | |
| | · | FC | DREIGN PATENT DOCUMENTS | | | T0.410 | 4 71011 |
| | DOCUMENT | DATE | COUNTRY | CLASS : | SUBCLASS | YES | LATION NO |
| | | - | | 1 | 1 | | |
| | | | | 1 | | | |
| | | | | | | | - |
| | | | | | | | |
| | | | | | | , | |
| | · | | | | | , | |
| | OTHER DOC | INSENTS (| Concluding Author Title Date Da | | | , | |
| | | | Including Author, Title, Date, Pe | | | , , , , , , , , , , , , , , , , , , , | |
| (кав | Shingubara et al, "Effec | ct of Pd Ca | (Including Author, Title, Date, Pe atalyst Adsorption on Cu Filling Chace, Conference Proceedings ULSI | aracteristics in E | lectroless F | | iety, pp. |
| /KAB/ | Shingubara et al, "Effect Advanced Metalization 229-234 Wang et al, "Electroles | ct of Pd Ca Conferences S Plating o | atalyst Adsorption on Cu Filling Cha | aracteristics in E XVI, 2001, Mate | lectroless F erials Resea | arch Soc | |
| | Shingubara et al, "Effer Advanced Metalization 229-234 Wang et al, "Electroles Plating", Eletrochemica Wang et al, "Suppressi Plating", Journal of App | ct of Pd Ca Conference s Plating of and Solid on of Nativolied Physi | atalyst Adsorption on Cu Filling Chace, Conference Proceedings ULSI of Copper on Metal-Nitride Diffusion d-State Letters, 6 (3), 2003, pp. C3 we Oxide Growth in Sputtered TaNics, vol. 94, no. 7, 1 October 2003, | aracteristics in E XVI, 2001, Mate Barriers Initiate 8-C41 films and its Ap pp. 4697-4701 | erials Resea ed by Displa plication to | arch Soc acement Cu Elec | troless |
| /KAB/ | Shingubara et al, "Effect Advanced Metalization 229-234 Wang et al, "Electroles Plating", Eletrochemica Wang et al, "Suppressi Plating", Journal of App Wang et al, "Influence vol. 42, 2003, pp. 1843 | ct of Pd Ca Conference S Plating of I and Solid on of Native of Surface -1846 | atalyst Adsorption on Cu Filling Chace, Conference Proceedings ULSI of Copper on Metal-Nitride Diffusion d-State Letters, 6 (3), 2003, pp. C3 we Oxide Growth in Sputtered TaN ics, vol. 94, no. 7, 1 October 2003, Oxide of Sputtered TaN on Displan | aracteristics in E XVI, 2001, Mate Barriers Initiate 8-C41 films and its Ap pp. 4697-4701 cement Plating | Electroless Ferials Researed by Displaplication to of Cu", Jpn. | arch Soc acement Cu Elect J. Appl. | Phys., |
| /KAB/ | Shingubara et al, "Effect Advanced Metalization 229-234 Wang et al, "Electroles Plating", Eletrochemica Wang et al, "Suppressi Plating", Journal of App Wang et al, "Influence of vol. 42, 2003, pp. 1843 Wang et al, "Highly Adi | ct of Pd Ca Conferences S Plating of I and Solid on of Native of Surface -1846 nesive Electors | atalyst Adsorption on Cu Filling Chace, Conference Proceedings ULSI of Copper on Metal-Nitride Diffusion d-State Letters, 6 (3), 2003, pp. C3 we Oxide Growth in Sputtered TaNics, vol. 94, no. 7, 1 October 2003, | aracteristics in EXVI, 2001, Materials In Barriers Initiate 8-C41 films and its Appp. 4697-4701 cement Plating an Ultra Thin Io | Electroless Ferials Researed by Displaced by Displaced Displaced Cluster Cluster Cluster Ferial Propriet Cluster Ferial Propri | arch Soc acement Cu Elec J. Appl. ter Bean | Phys., |
| /KAB/ /KAB/ /KAB/ | Shingubara et al, "Effect Advanced Metalization 229-234 Wang et al, "Electroles Plating", Eletrochemica Wang et al, "Suppressi Plating", Journal of App Wang et al, "Influence vol. 42, 2003, pp. 1843 Wang et al, "Highly Adr Pd Catalytic Layer for S | ct of Pd Ca Conferences S Plating of I and Solid On of Native Diled Physion of Surface -1846 Desive Elector | atalyst Adsorption on Cu Filling Chace, Conference Proceedings ULSI of Copper on Metal-Nitride Diffusion d-State Letters, 6 (3), 2003, pp. C3 // e Oxide Growth in Sputtered TaN cs, vol. 94, no. 7, 1 October 2003, Oxide of Sputtered TaN on Displacetroless Cu Layer Formation Using | aracteristics in EXVI, 2001, Materials In Barriers Initiate 8-C41 films and its Appp. 4697-4701 cement Plating an Ultra Thin Icol. Physics, vol. 4 | electroless Ferials Researed by Displaced Displaced Cluster Cl | arch Soc acement Cu Elec J. Appl. ter Bean | Phys., |

Form PTO-FB-A820 (Also PTO-1449)